REMARKS/ARGUMENTS

Claim 1 is unchanged. Claims 2-17 have been added.

It is noted that the specification filed in this case is in the form of the substitute specification that was filed on February 18, 2004 in the parent application (No. 10/262,567). That substitute specification was accepted by the Examiner in the parent case.

The amendments to the specification made herein are intended to conform the specification to the amendments in the drawings, described in the preceding section, and to correct several remaining clerical and syntactical errors. No new matter has been added.

A complete set of formal drawings is submitted herewith.

Should the Examiner have any questions about any of the amendments made herein, the Examiner is invited to call the undersigned at (408) 982-8201.

CERTIFICATE OF MAILING BY "FIRST CLASS"

I hereby certify that this paper or fee is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the below date.

Attorney for Applicant(s) — Date of Signature: 8/8/05

Respectfully submitted,

David E. Steuber
Attorney for Applicant(s)
Reg. No. 25,557

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Amendments to the Drawings:

The enclosed Submission of Formal Drawings includes changes to Figs. 14A-14E, 14H-14P, 15A, 16A, 16B, 16D, 16F, 17P-17CC (now Figs. 17O-17BB), 18B (now Fig. 18B-4), 18C, 18H, 19H, 33D and 64B.

The following is an itemization of the changes:

In Figs. 14A-14E, 14H-14P, 15A, 16A, 16B, 16D and 16F, in a number of instances the reference numeral PW5 has been changed to PW5B, the reference numeral NW5 has been changed to NW5B, the reference numeral PW12 has been changed to PW12B, and the reference numeral NW12 has been changed to NW12B, as shown on the enclosed Annotated Sheets. These changes are clearly supported, for example, at page 36, lines 14-17, of the substitute specification filed February 18, 2004, where it is indicated that the suffix "B" is used to denote an implanted layer of dopant as opposed to a "well" of dopant. In any event, these changes are merely changes in labeling and as such do not constitute new matter.

Figs. 17P-17CC have been renumbered as Figs. 17O-17BB, respectively, to rectify the omission of Fig. 17O from the application as filed.

To make the drawings more legible, Figs. 18A and 18B have each been split into four drawings, designated Figs. 18A-1 to 18A-4 and Figs. 18B-1 to 18B-4, respectively. The subject matter in Figs. 18A-1 to 18A-4 and 18B-1 to 18B-3 is unchanged. In Fig. 18B-4, the reference numeral 354M has been replaced by the numeral 354L. The numeral 354M was an error. There is no such reference numeral in the application as filed.

In Fig. 18C, the reference numeral 364P, which is referred to at page 66, line 4, of the substitute specification, has been added, and the designation of the source-body contact has been corrected from "S/D" to "S/B".

In Fig. 18H, reference numeral applicable to the well NW5 has been changed from 354R to 354S to eliminate the conflict with the similarly numbered element in Fig. 18G; and

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the reference numeral applicable to the deep N layer has been changed from 390G to 390H to eliminate the conflict with the similarly numbered element in Fig. 35A.

In Fig. 19H, the reference numeral 387 has been corrected to 320 to correspond to the designation of the DMOS transistor at page 70, line 7, of the substitute specification.

In Fig. 33D, the reference numeral 486 has been deleted. It is not referenced in the substitute specification.

In Fig. 64B, the description of the 5 volt transistor 306 as been corrected to "PNP."

All of the foregoing changes are shown in red in the enclosed Annotated Marked-up Drawings.

Finally, to place the drawings in sequential order, sheets 215-218 (Figs. 17V-17CC) of have been renumbered as sheets 75-78 (renumbered Figs. 17U-17BB), and sheet 219 (Fig. 18H) has been renumbered as sheet 92.

All of the foregoing amendments are incorporated in the Submission of Formal Drawings, enclosed herewith.

Attachment: Annotated Sheets Showing Changes

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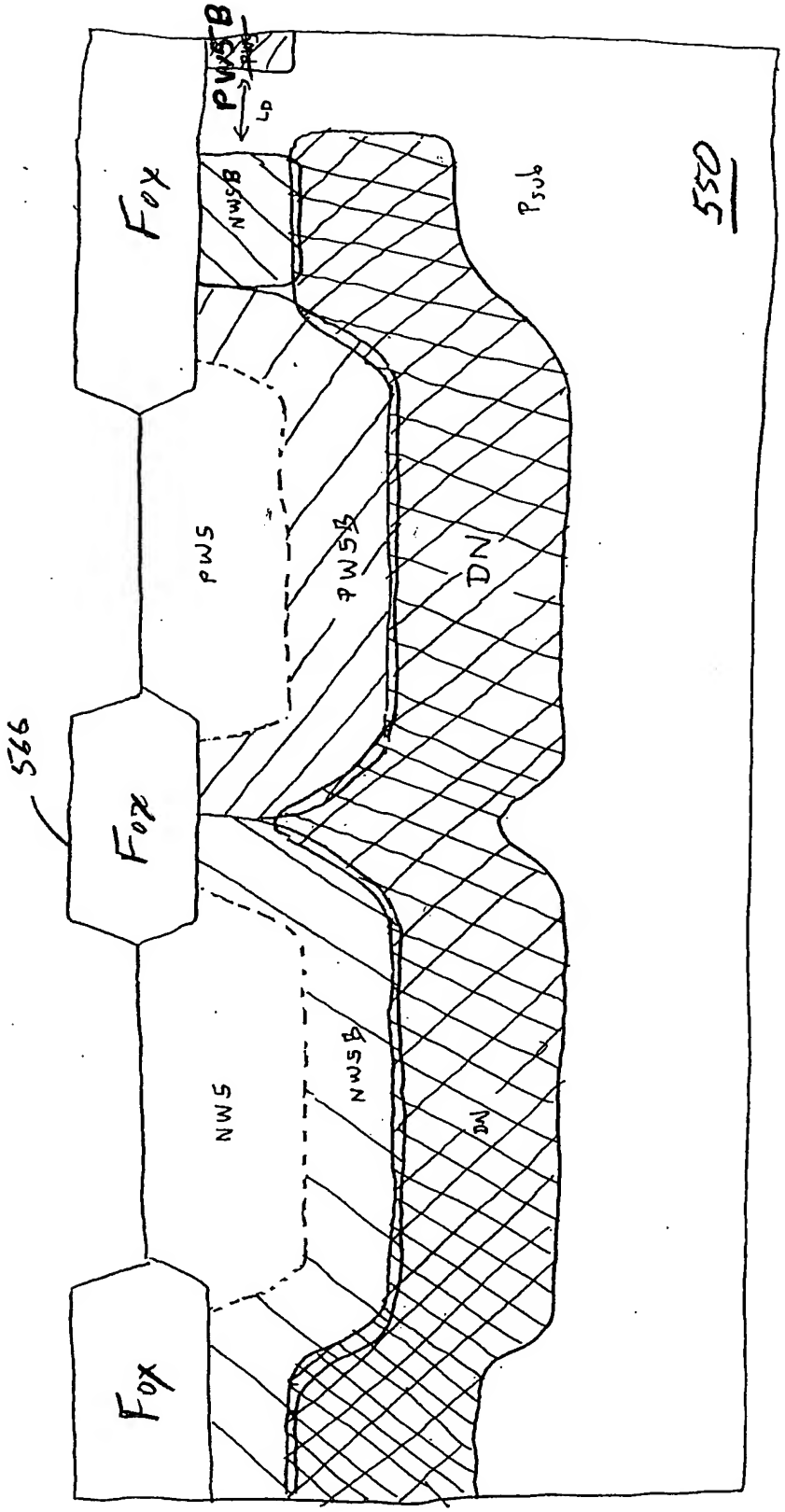


Fig 14A

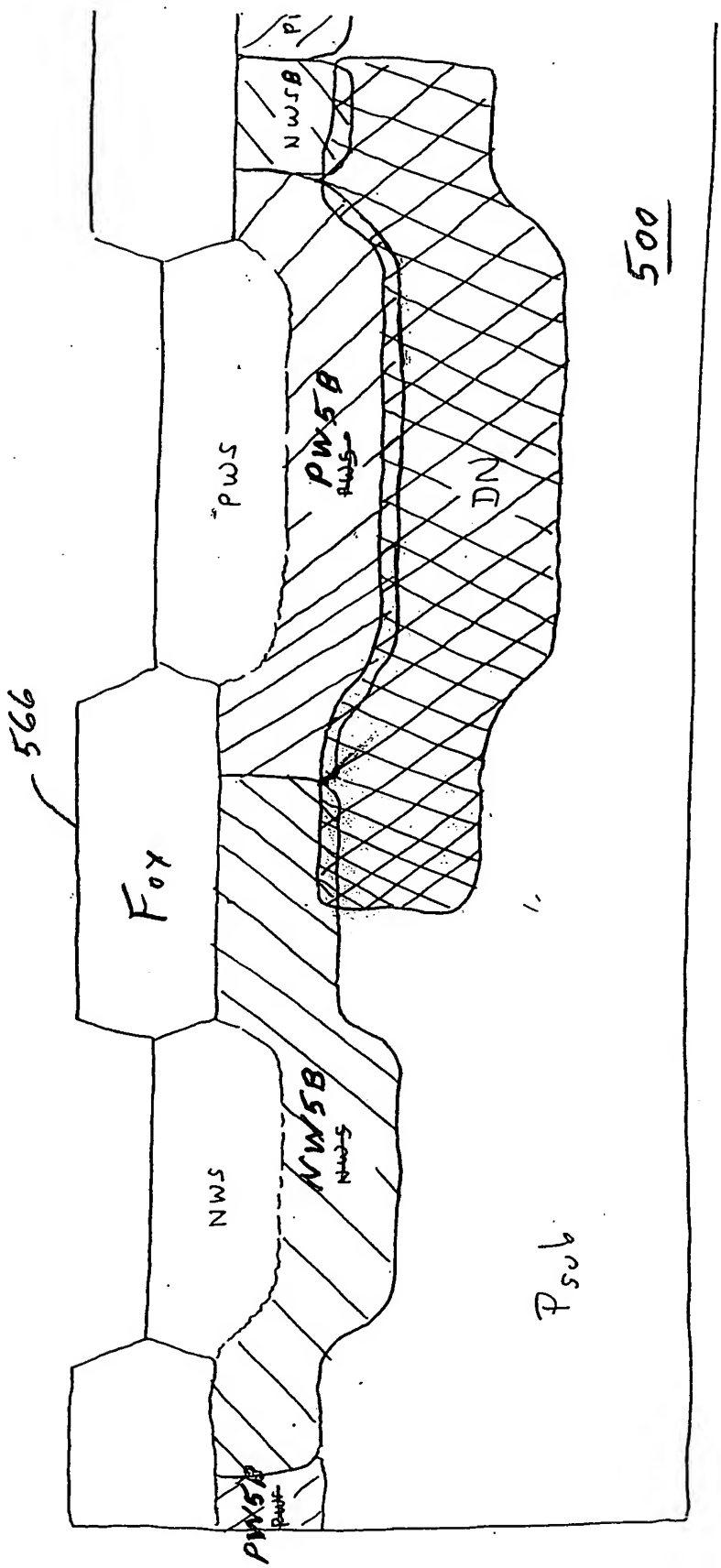


Fig. 14B

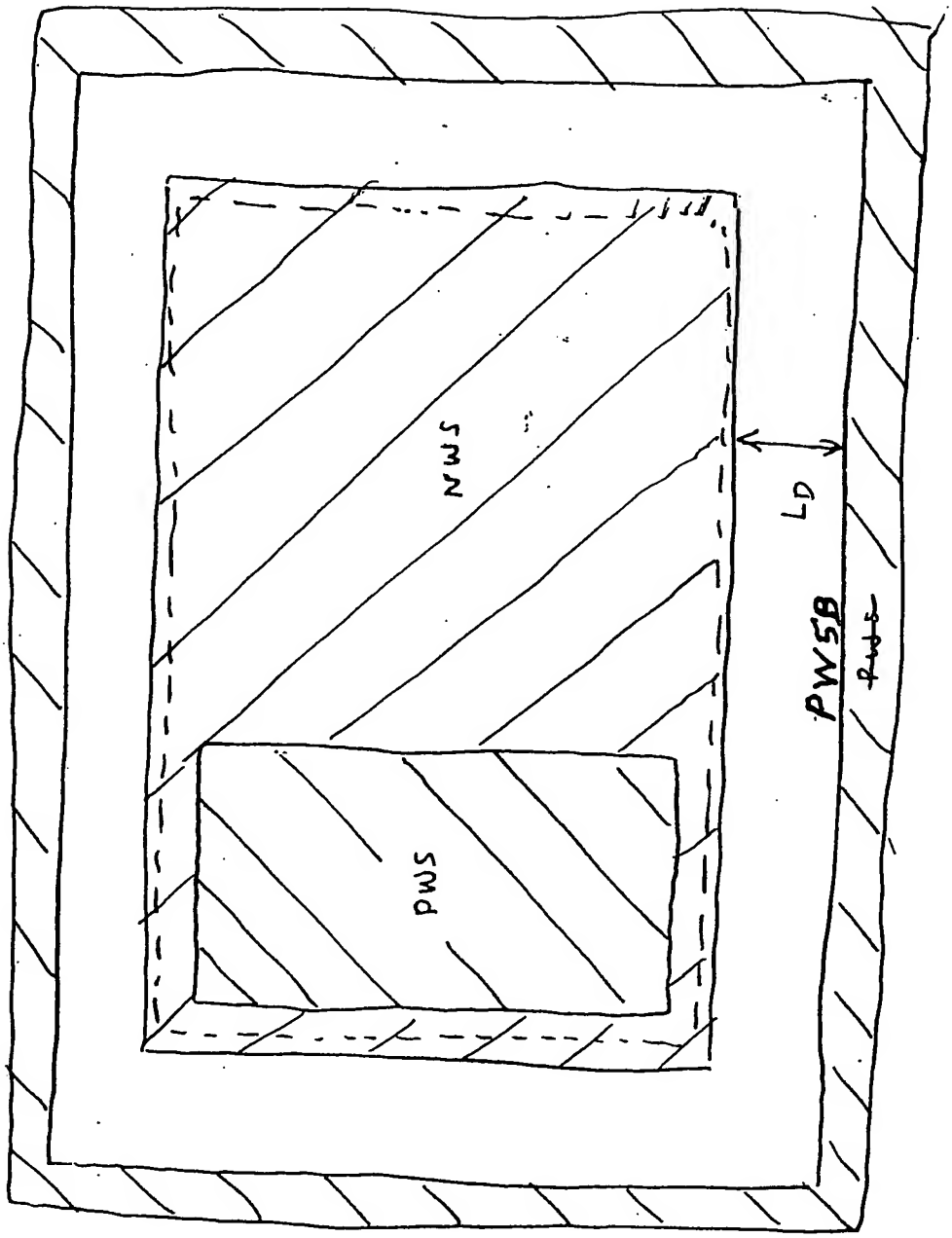


Fig. 14C

Fig. 14E

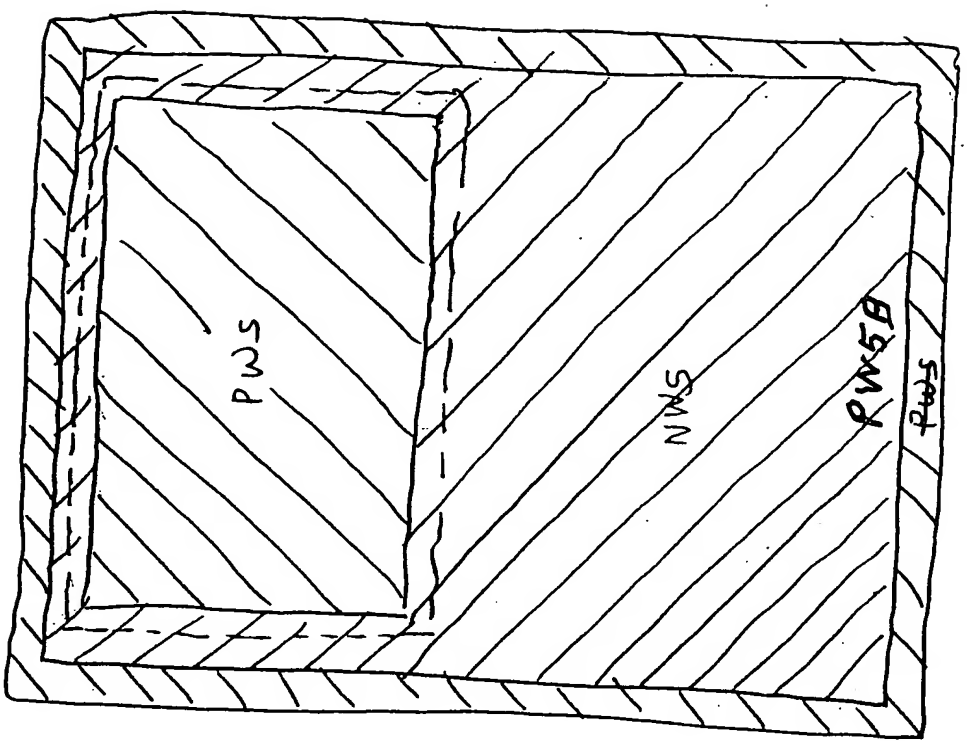
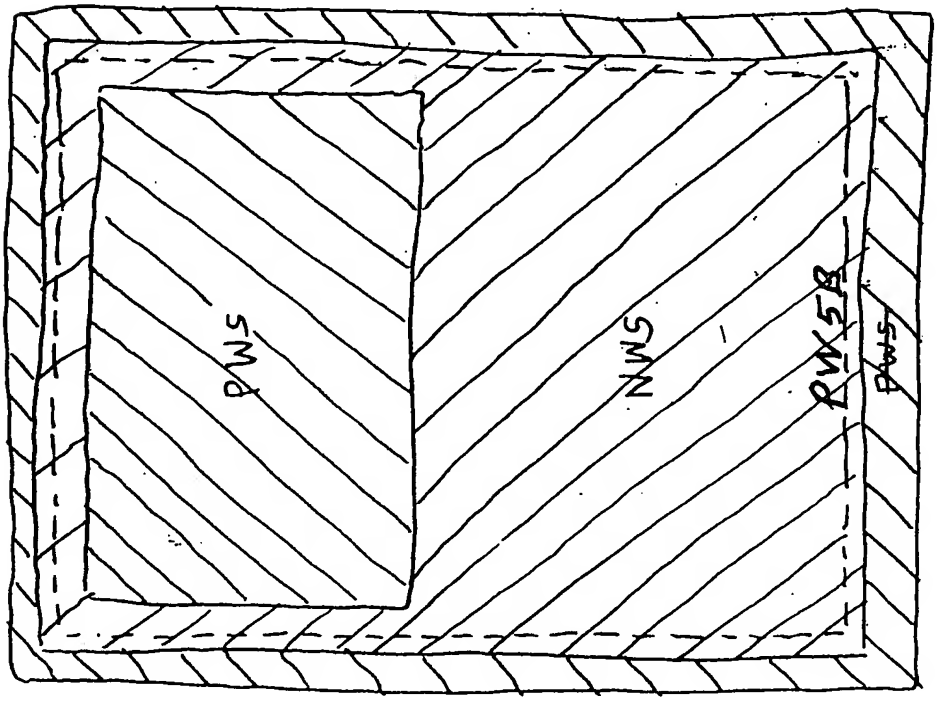


Fig. 14D



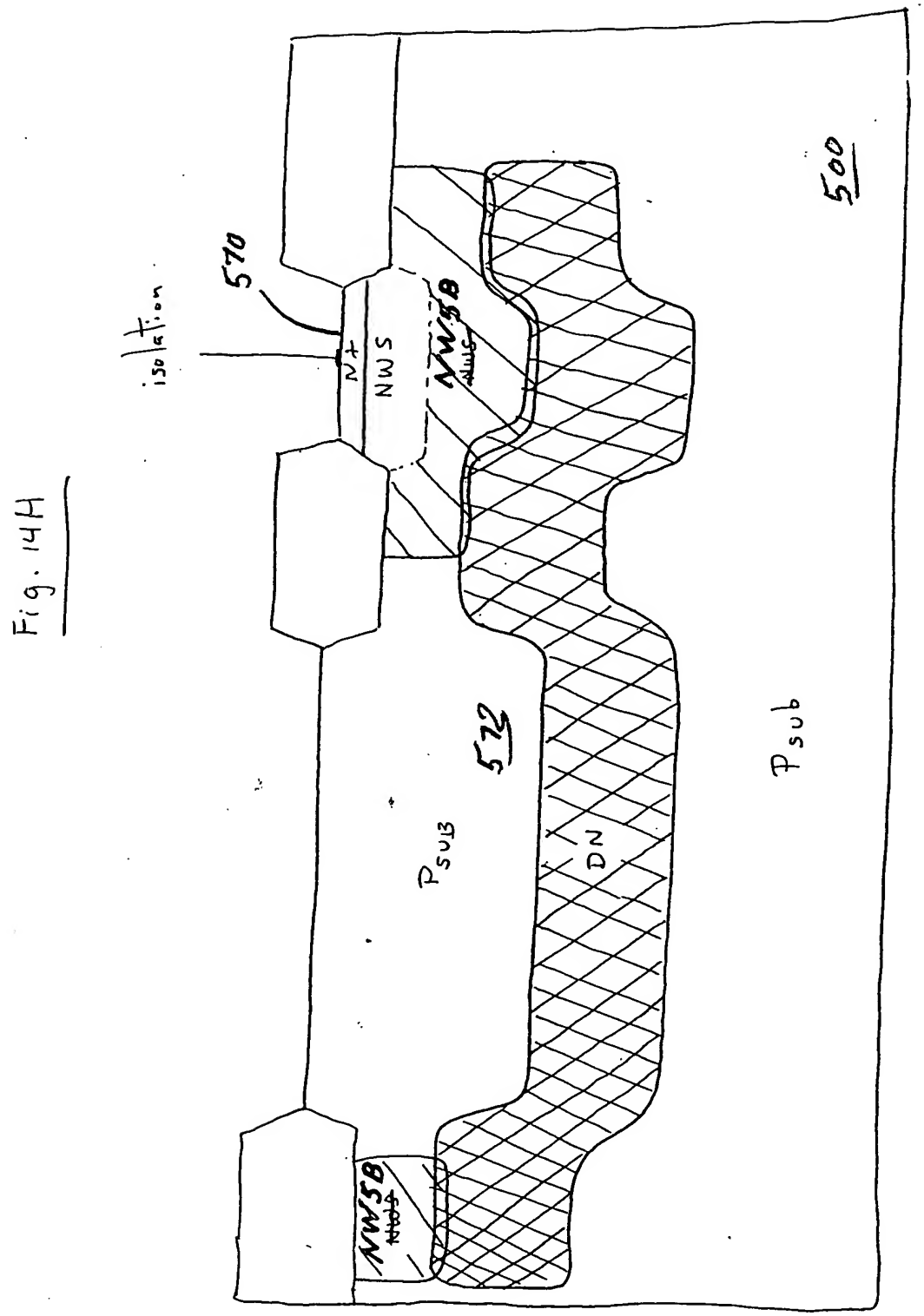


Fig. 14H

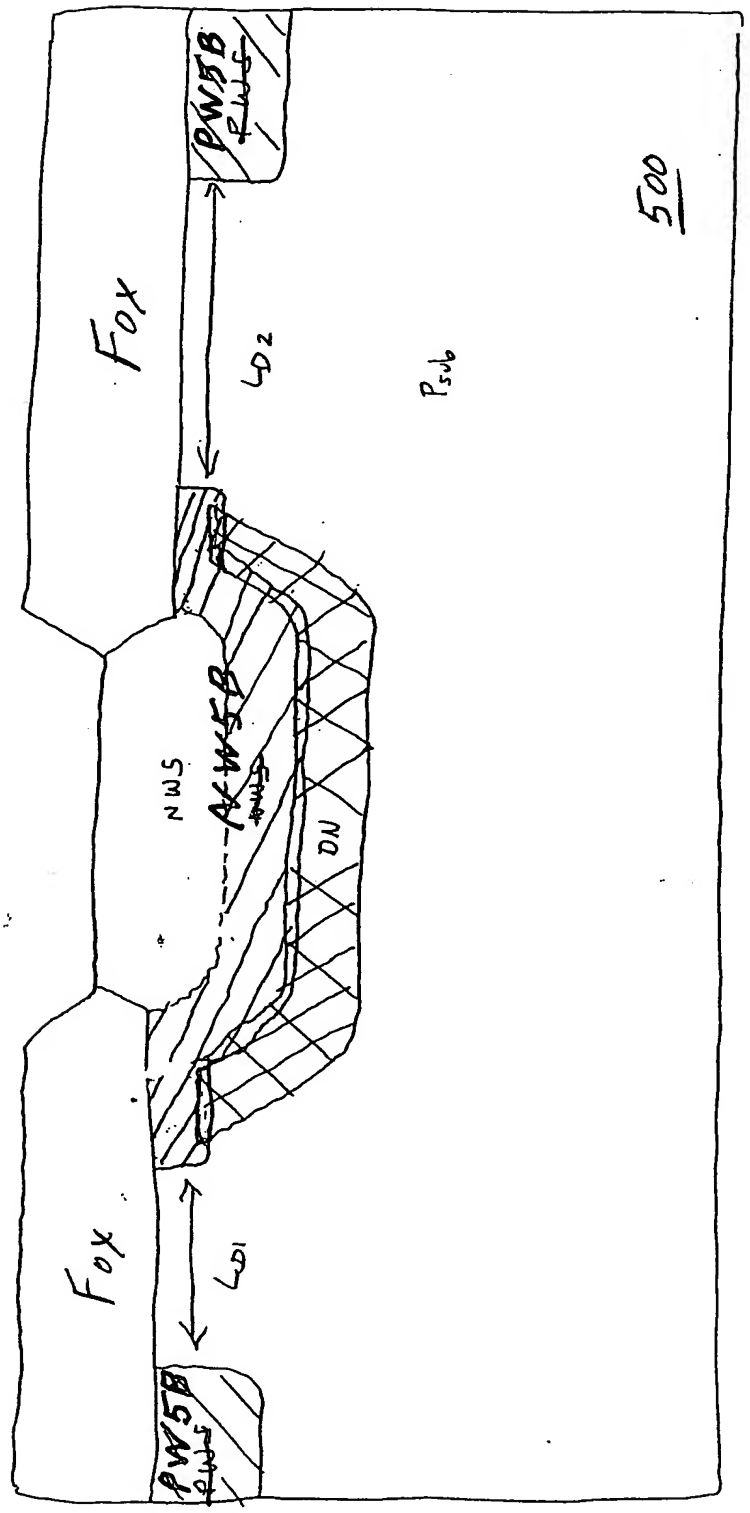


Fig. 14I

Fig. 14J

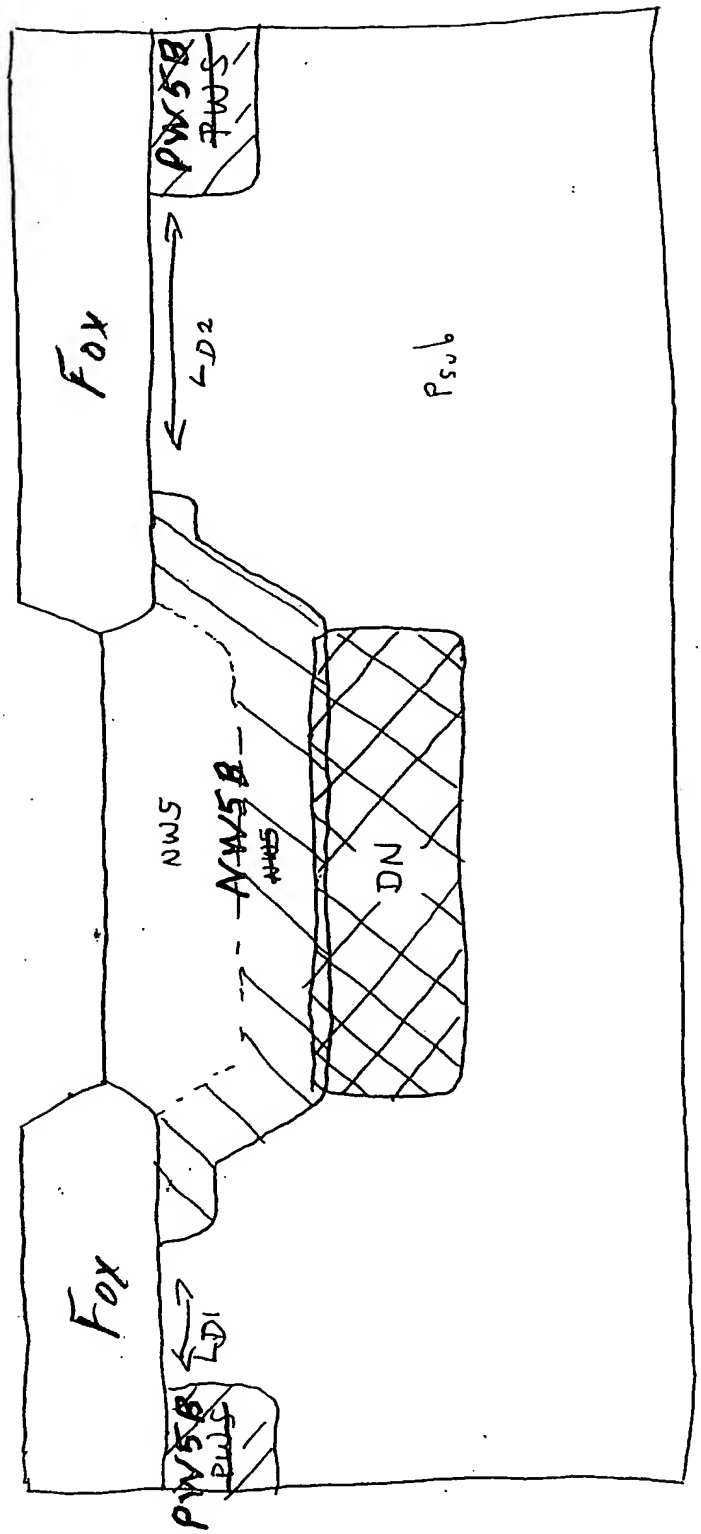


Fig. 14K

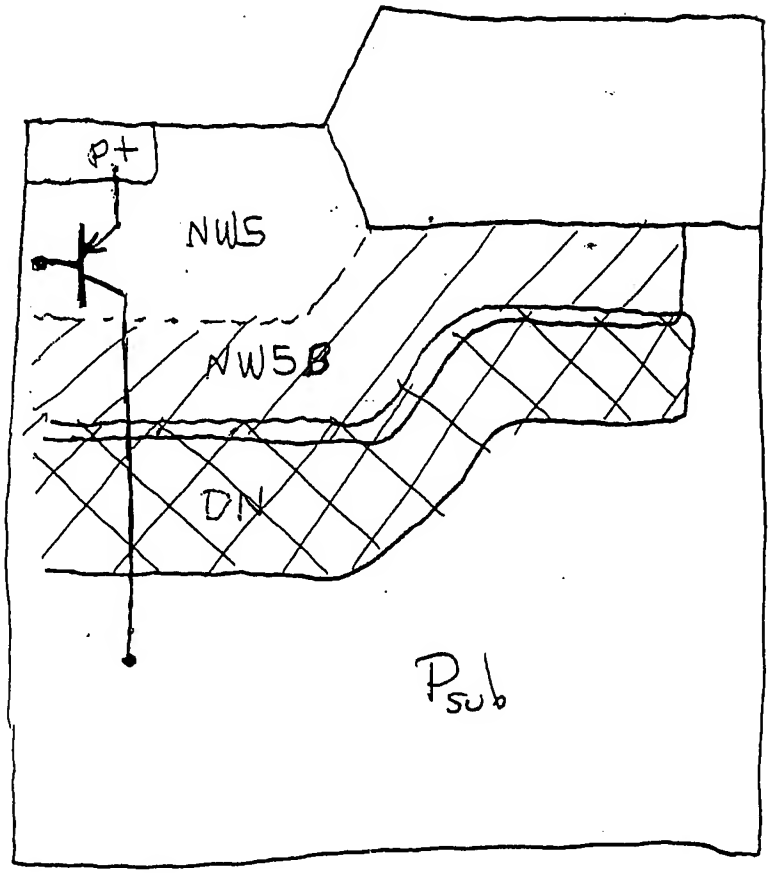
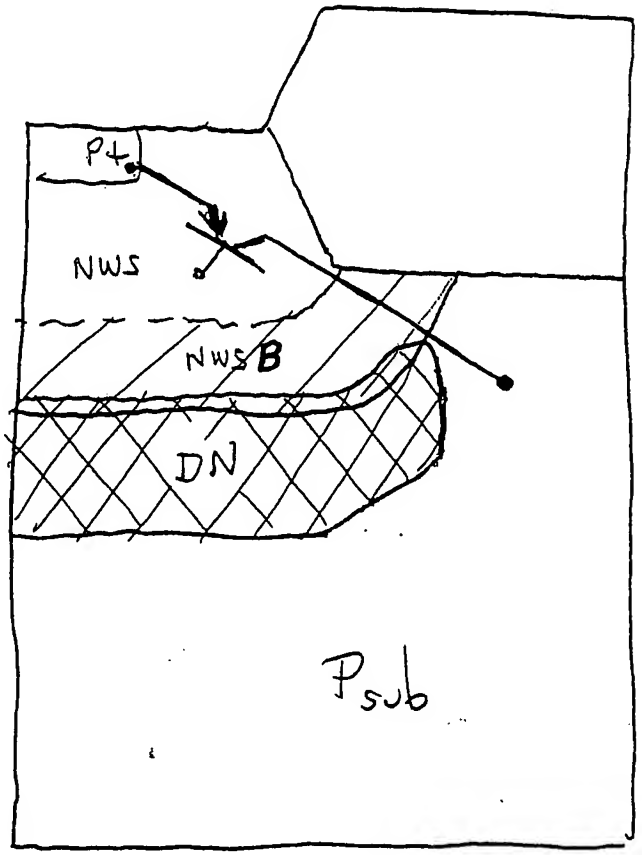


Fig. 14L



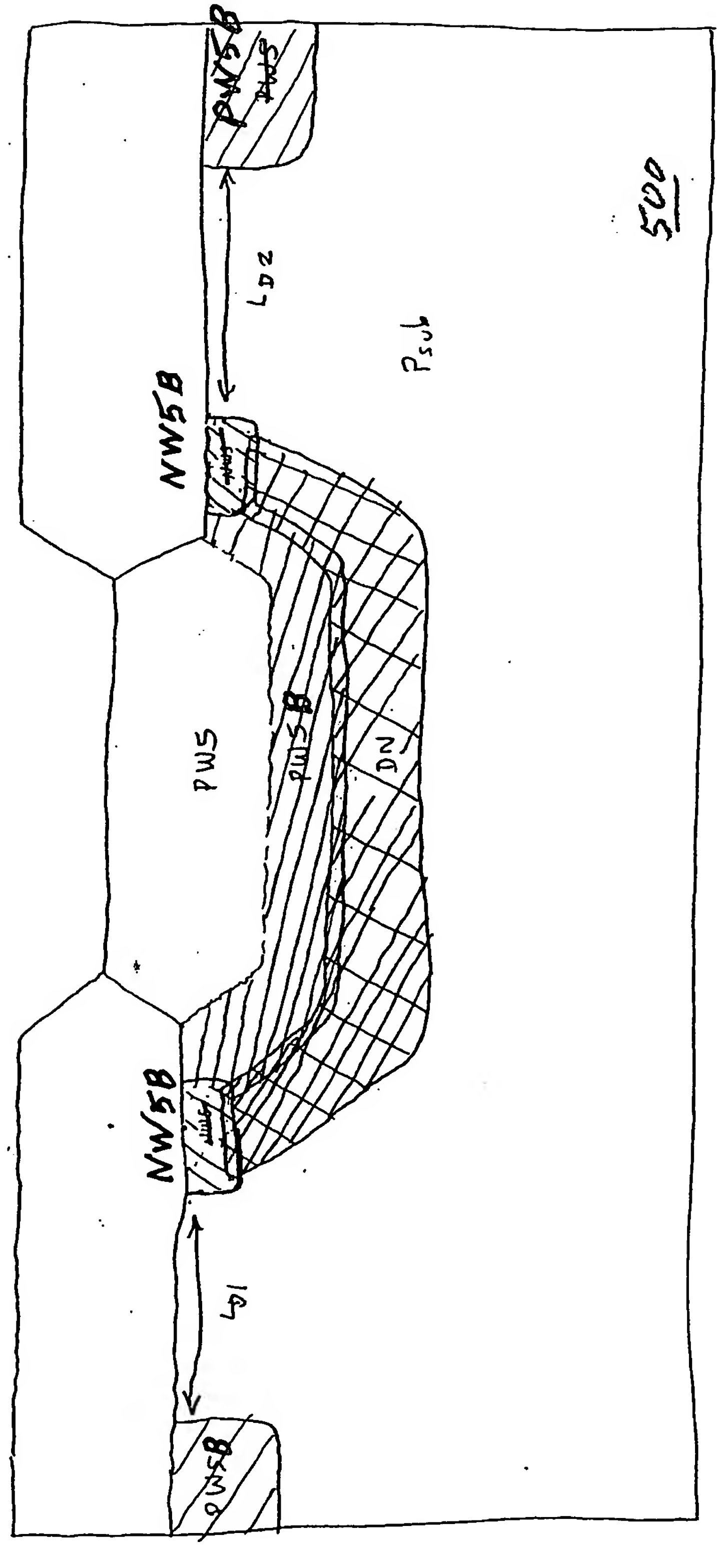


Fig. 14.M

Fig. 14N

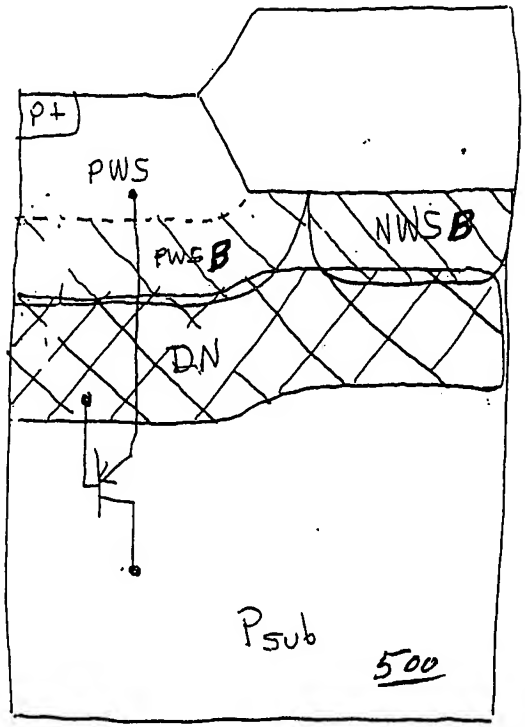


Fig. 14O

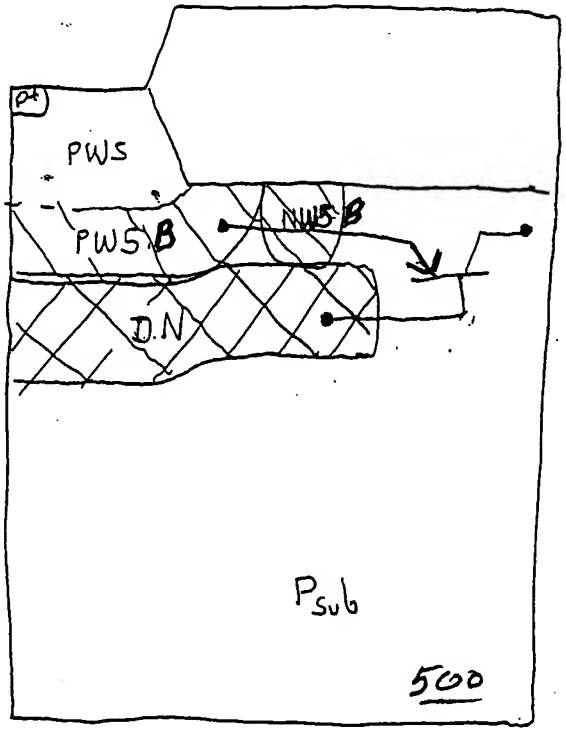
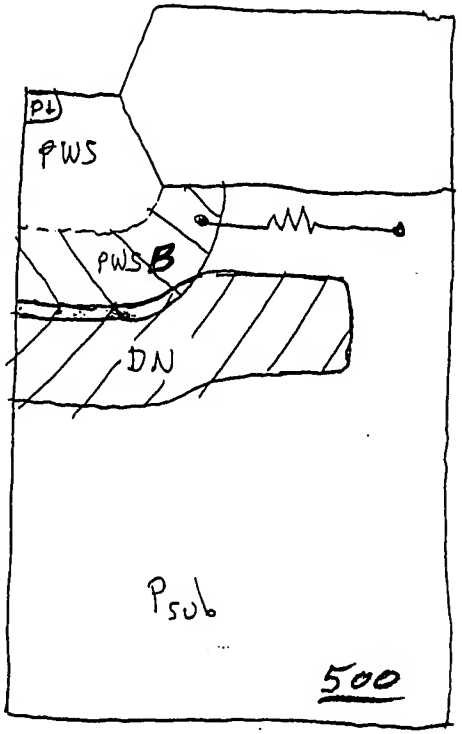


Fig. 14P



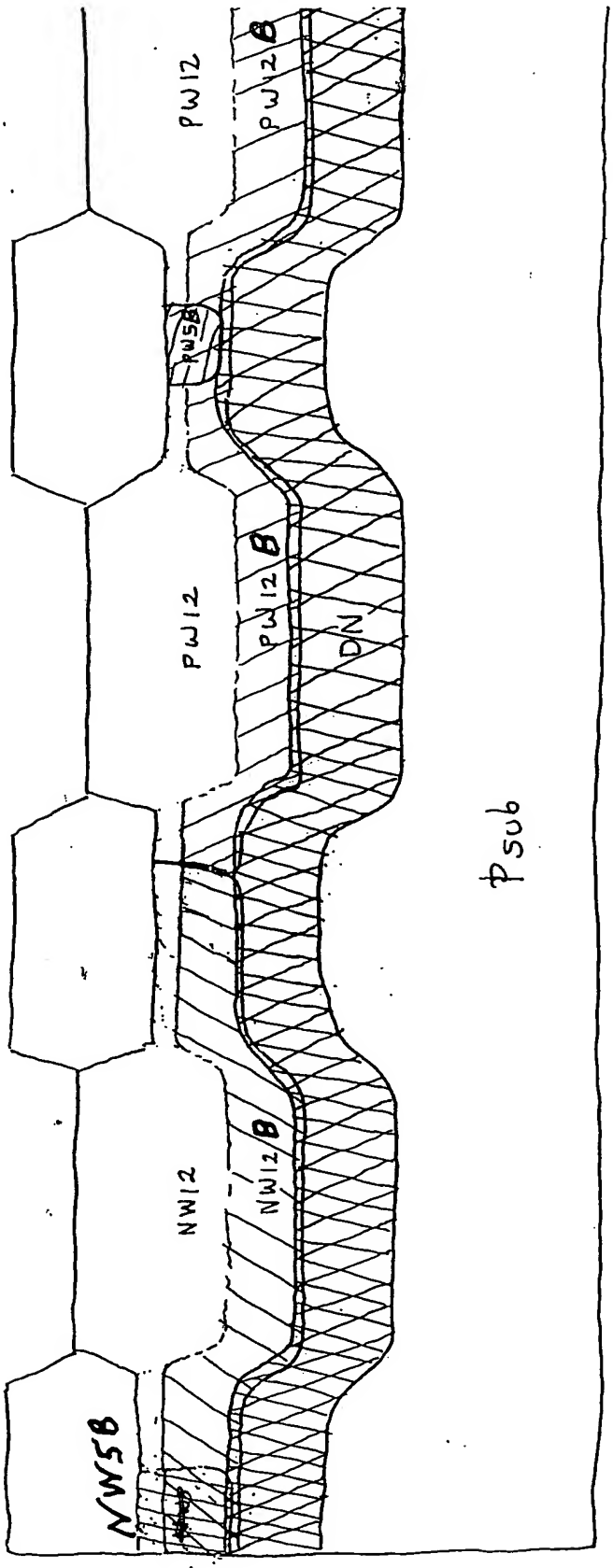


Fig. 15A

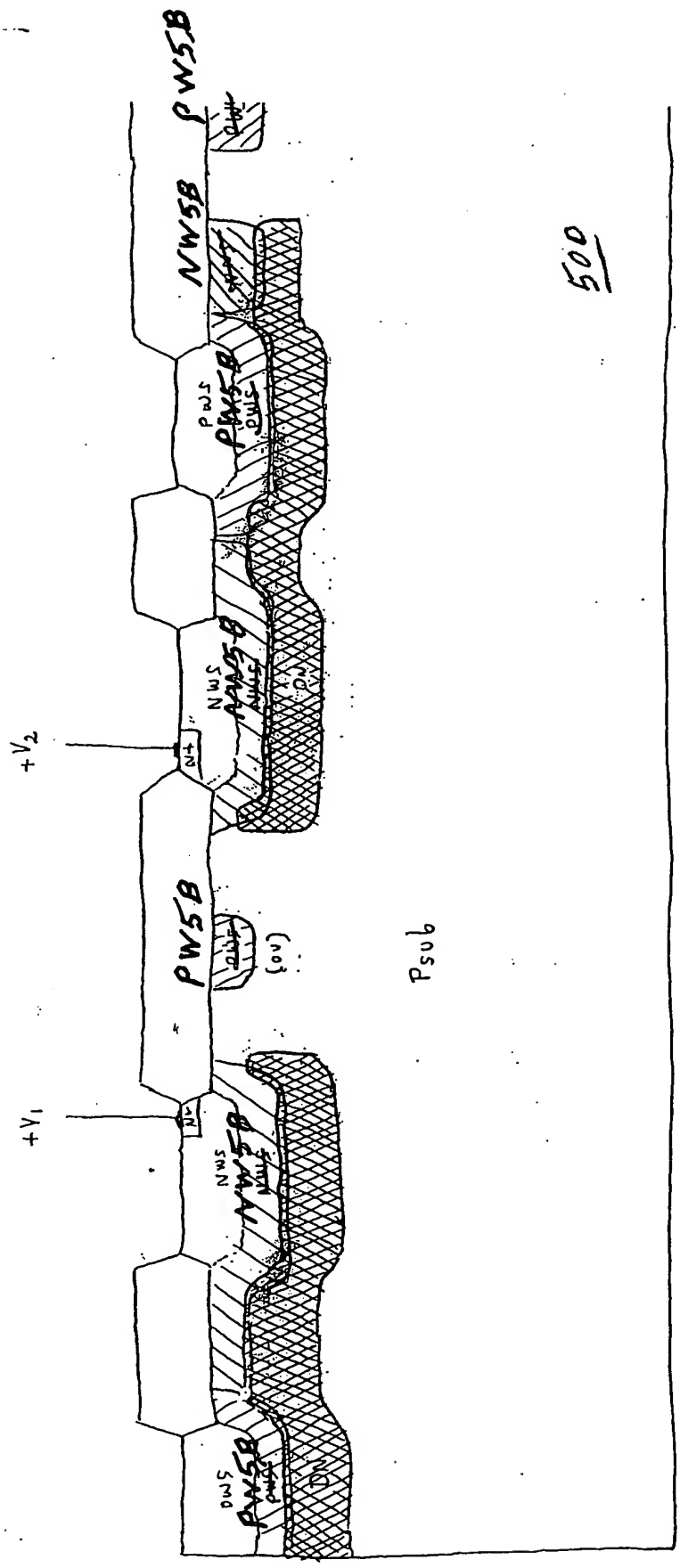


Fig. 16A

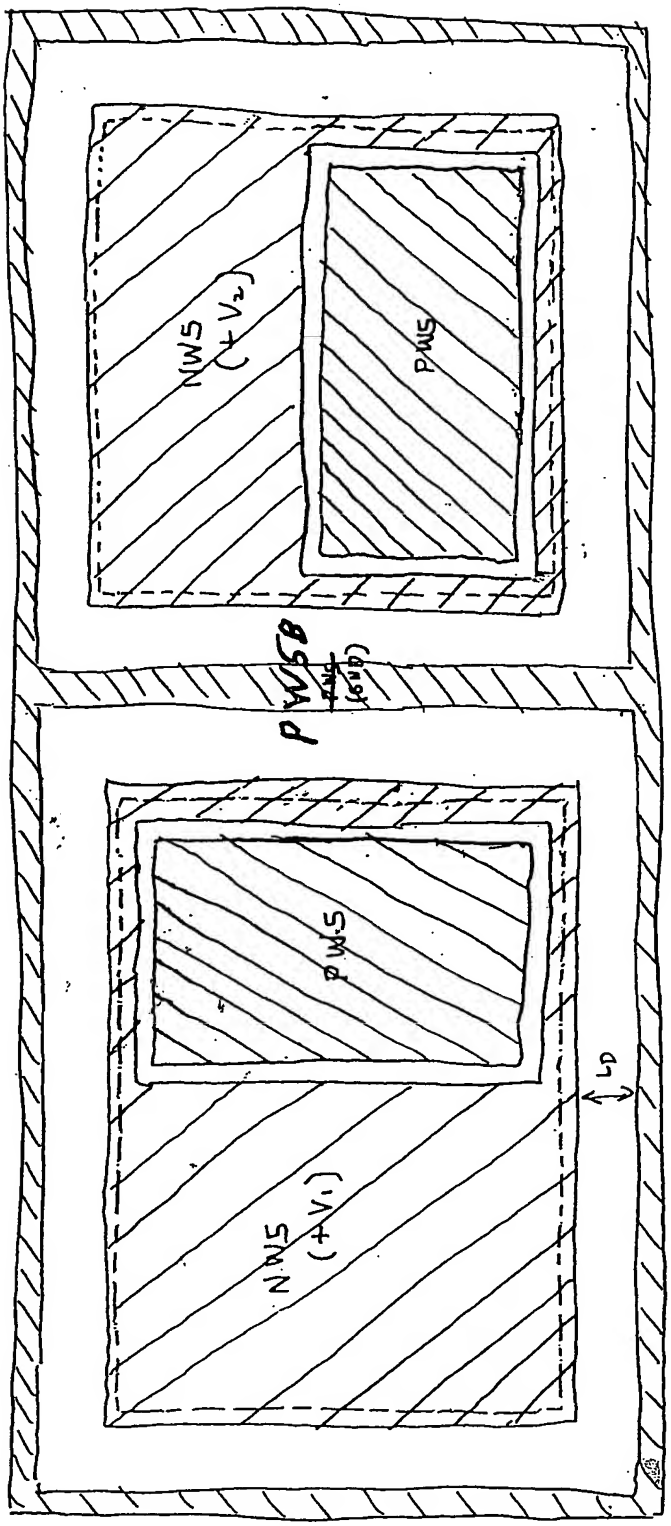


Fig. 16B

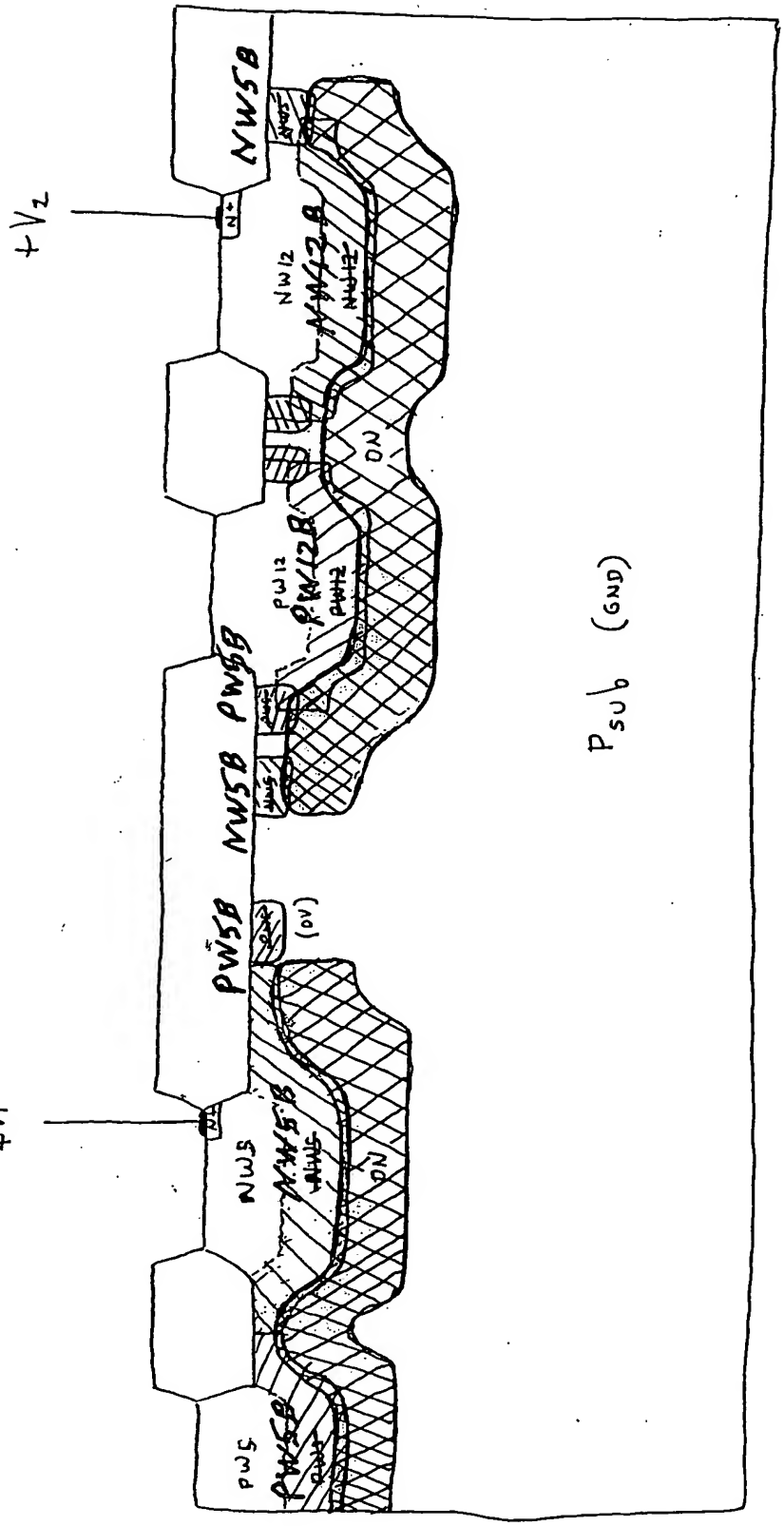

+V2
+V1
NWSB
PWSB
NWSB
PWSB
NW12
PW12
NW12
PW12
NWS
PWS
NWS
PWS
N+
P+
(0V)
ON
ON
PSUb (GND)

Fig. 16D

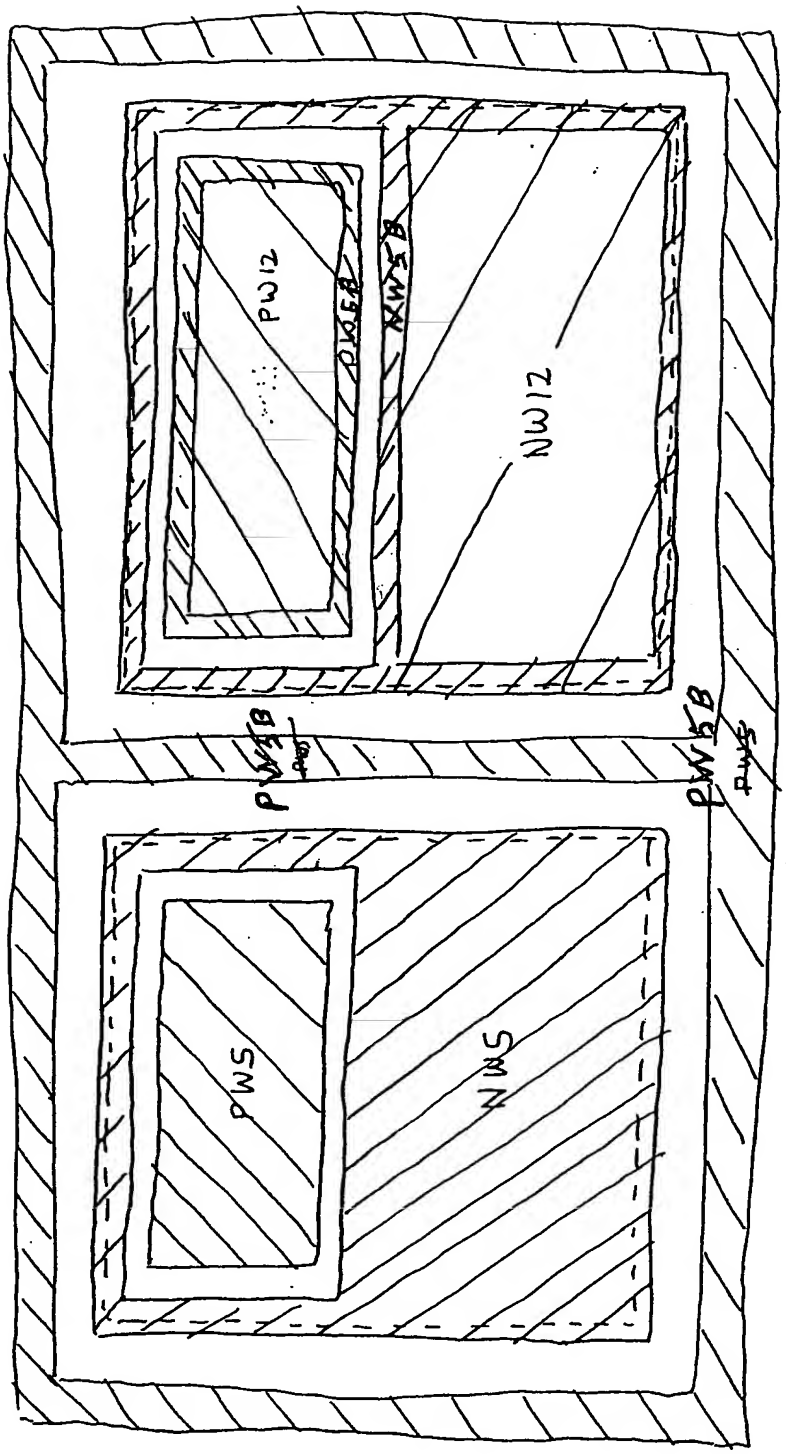


Fig. 16F

Fig. 17O

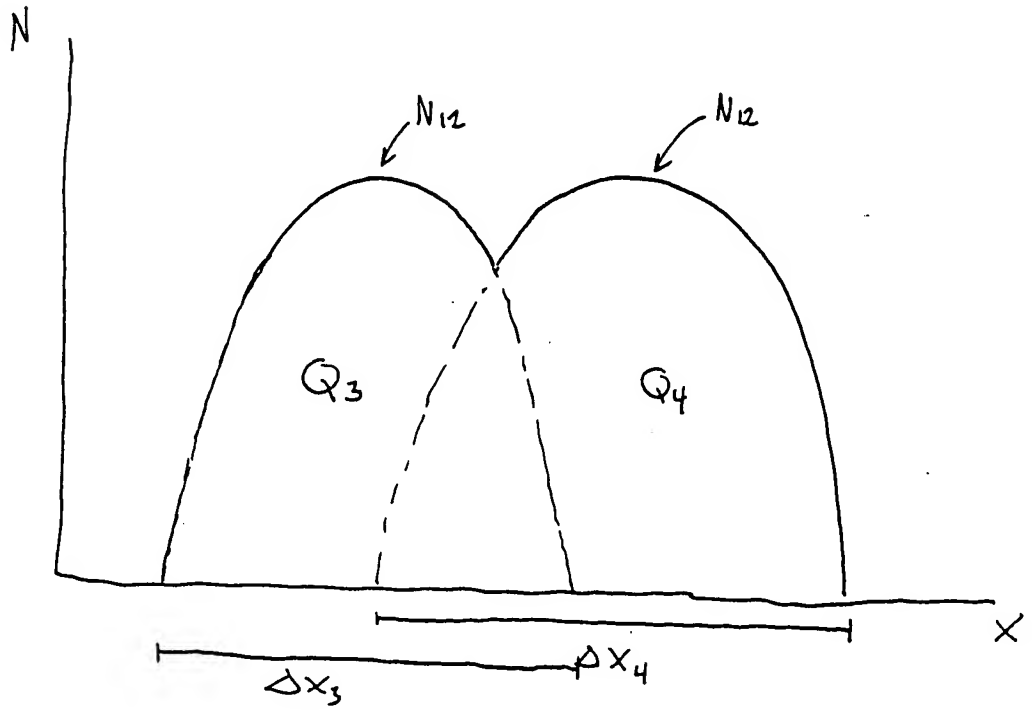
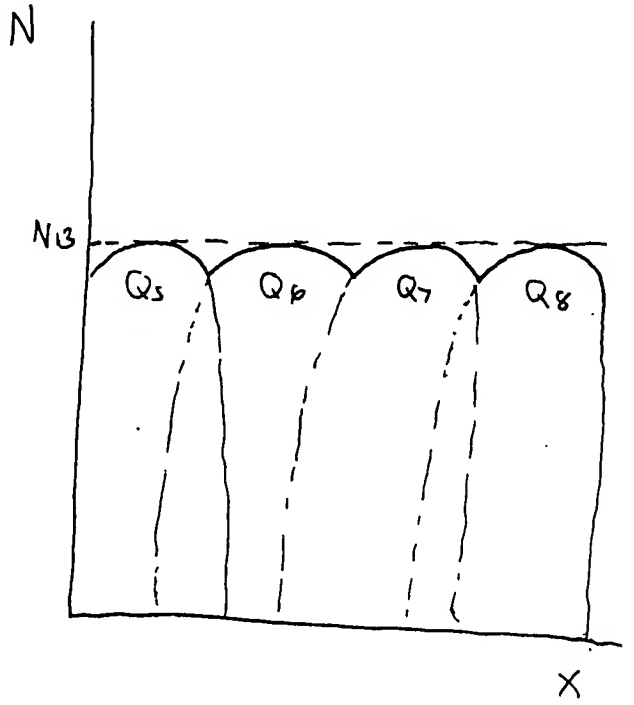
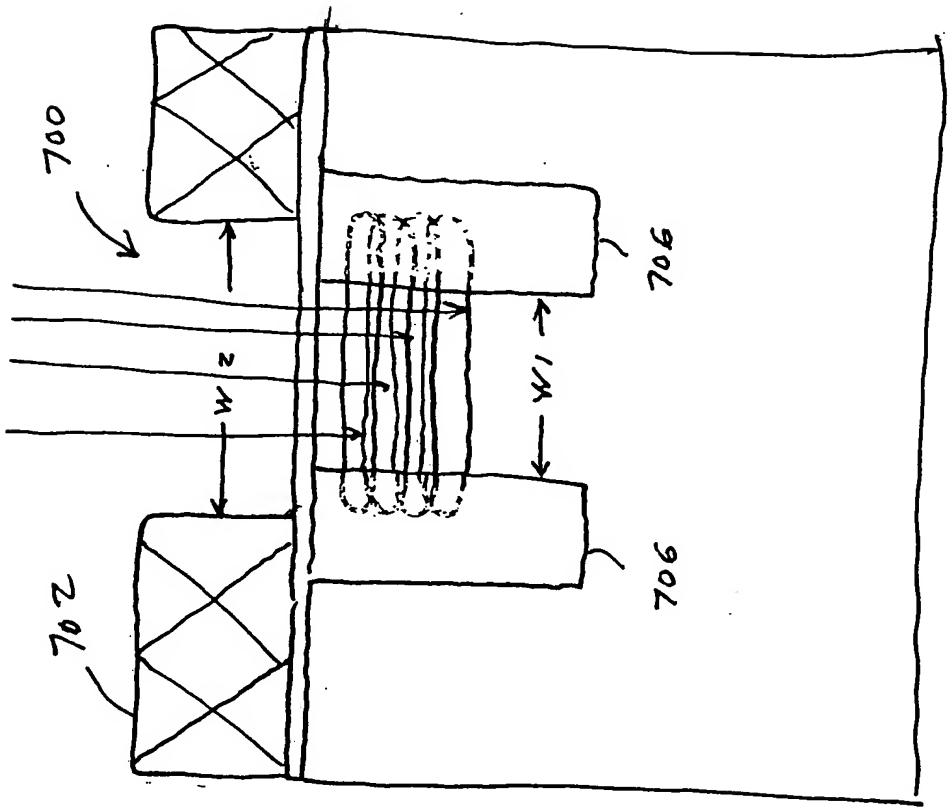


Fig. 17P

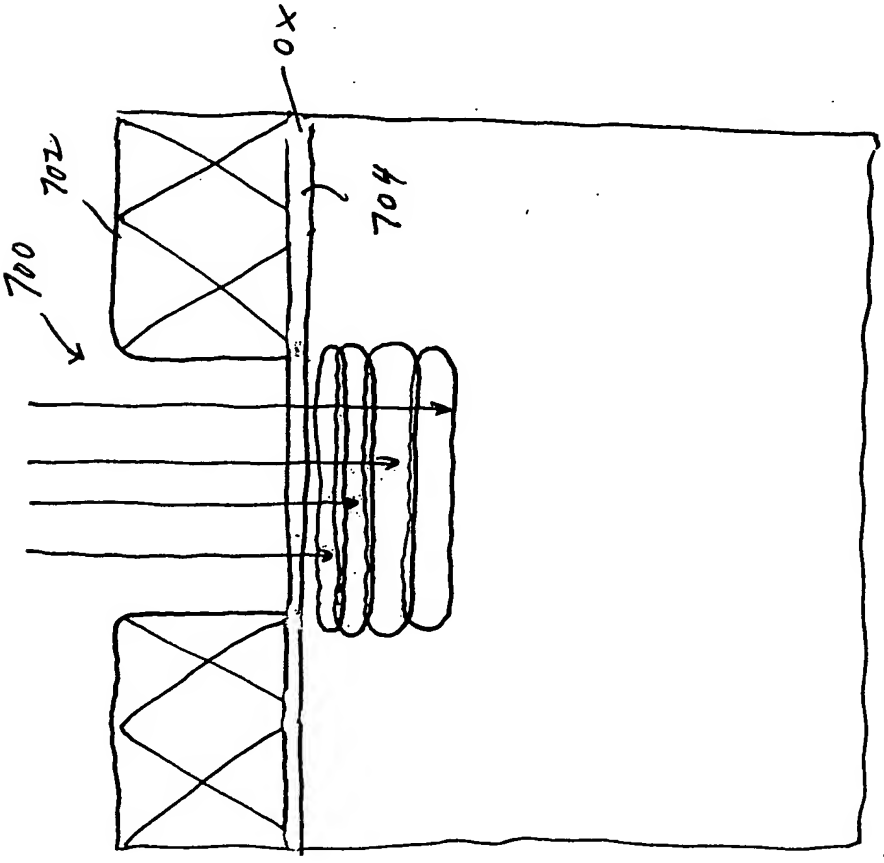


73/219

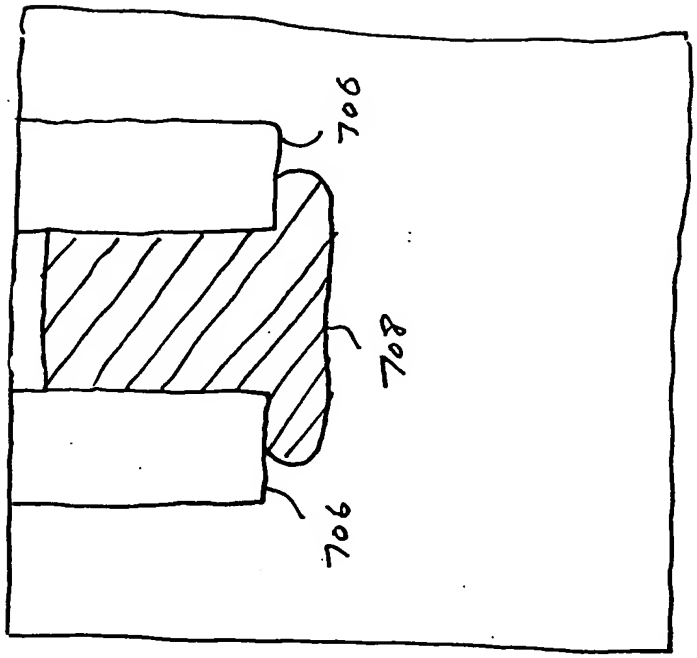
R
Fig. 17B



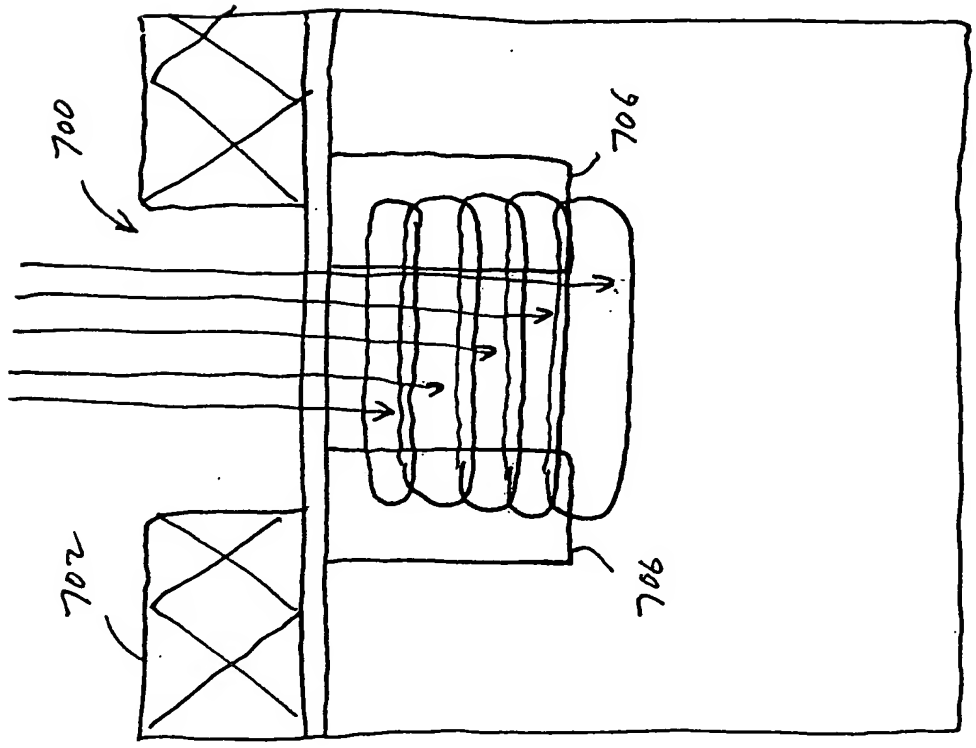
Q
Fig. 17A



T
Fig. 17B



S
Fig. 17A



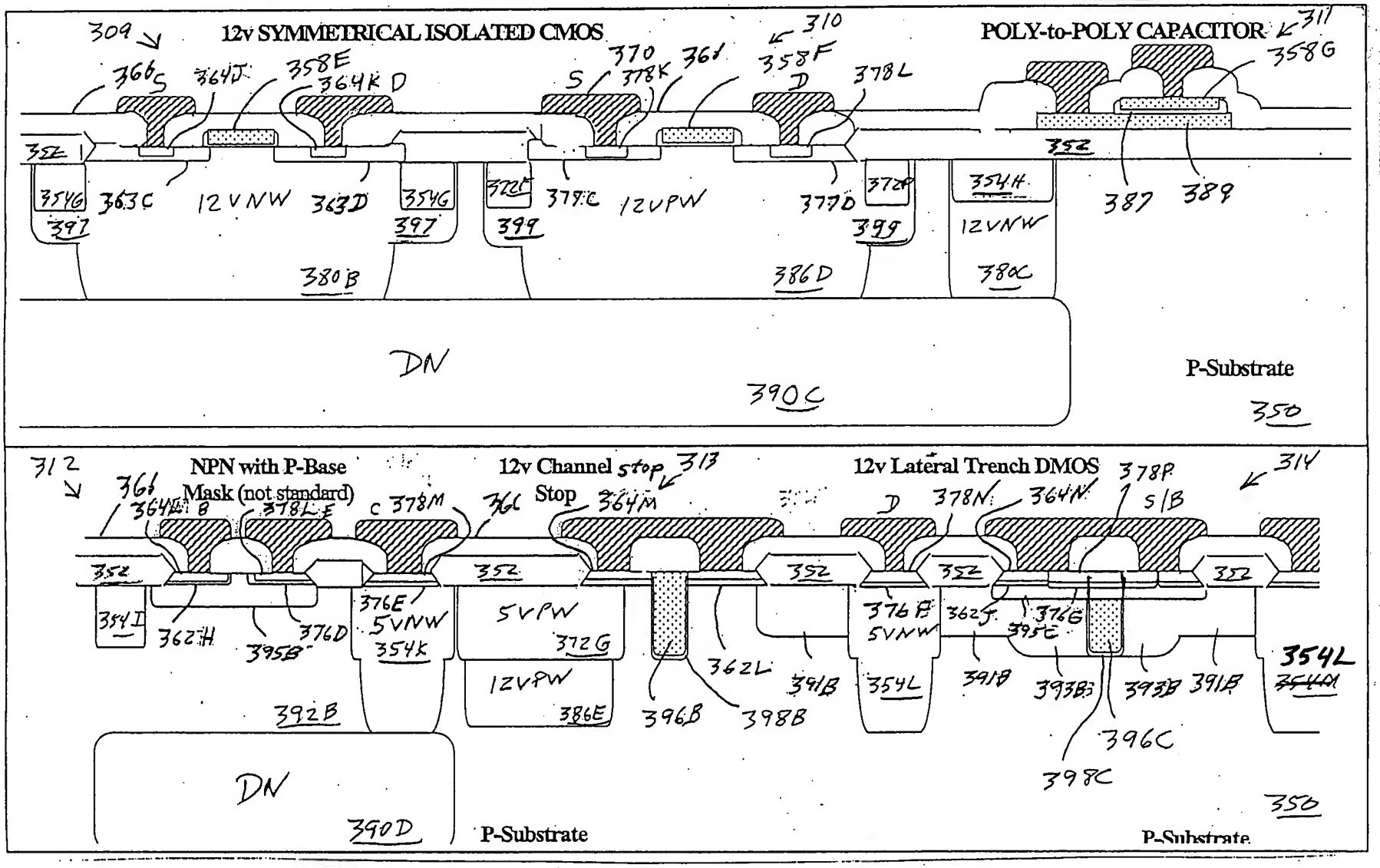

309
12v SYMMETRICAL ISOLATED CMOS
310
POLY-to-POLY CAPACITOR
311
366S
364J
358E
364K D
370
S
378K
361
358F
D
378L
358G
352
354G
363C
12VNW
363D
354G
372F
379C
12VPW
377D
372F
354H
387
389
397
397
399
399
12VNW
380B
386D
380C
DN
390C
P-Substrate
350
312
NPN with P-Base
Mask (not standard)
12v Channel stop
313
Stop
12v Lateral Trench DMOS
314
361
364L B
378L E
C 378M
361
364M
D
378N
364N
378P
S
B
352
352
352
352
352
354I
362H
395B
376D
376E
5VNW
354K
5VPW
372G
12VPW
386E
362L
391B
376F
5VNW
362F
376G
395C
354L
391B
393B
393B
391B
354L
392B
396B
398B
396C
398C
DN
390D
P-Substrate
P-Substrate
350

Fig. 18B

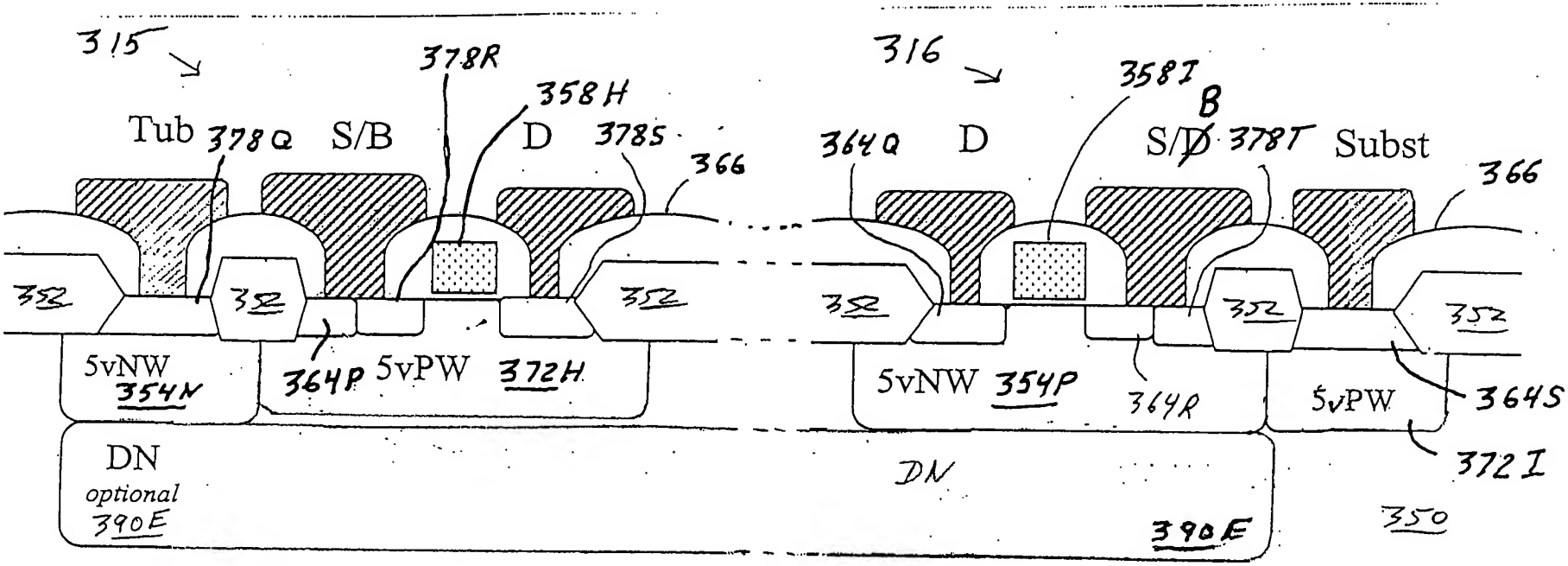

315
316
378R
358H
358I
B
Tub
378Q
S/B
D
378S
364Q
D
S/D
378T
Subst
366
366
352
352
352
352
352
352
5vNW
354N
364P
5vPW
372H
5vNW
354P
364R
5vPW
364S
372I
DN
optional
390E
DN
390E
350

Fig. 18C

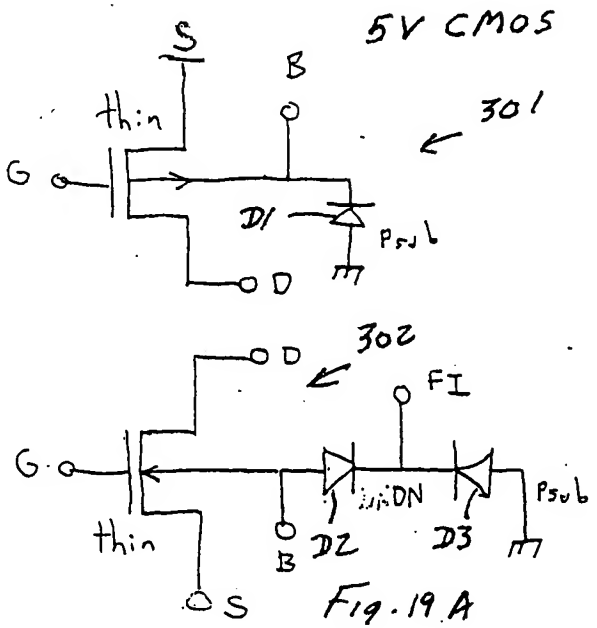


Fig. 19A

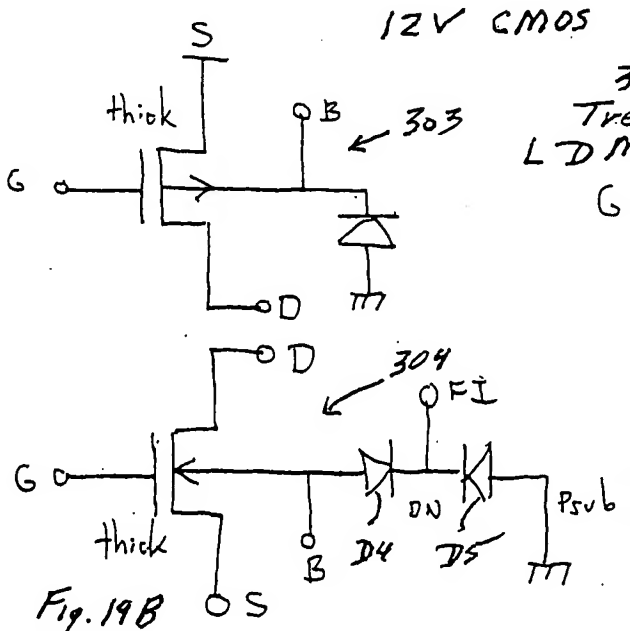


Fig. 19B

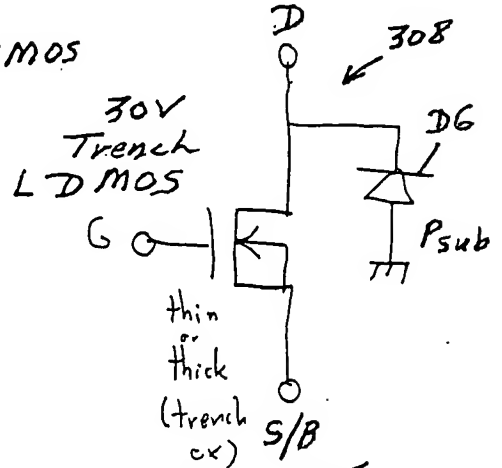


Fig. 19E

5V NPN

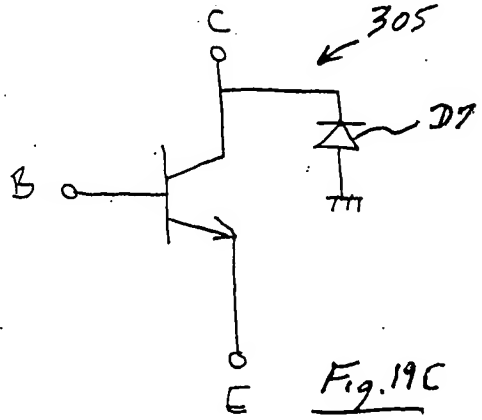


Fig. 19C

5V PNP

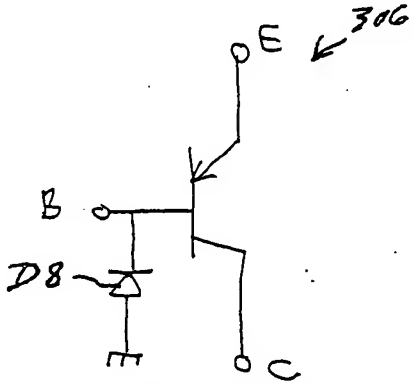


Fig. 19D

30V LDMOS

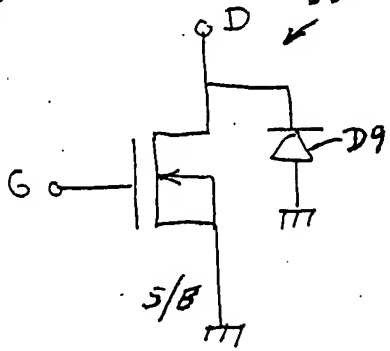


Fig. 19H

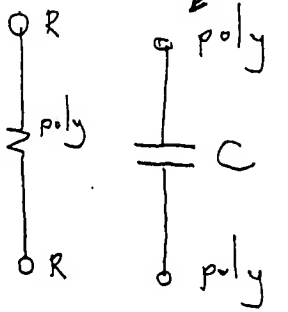
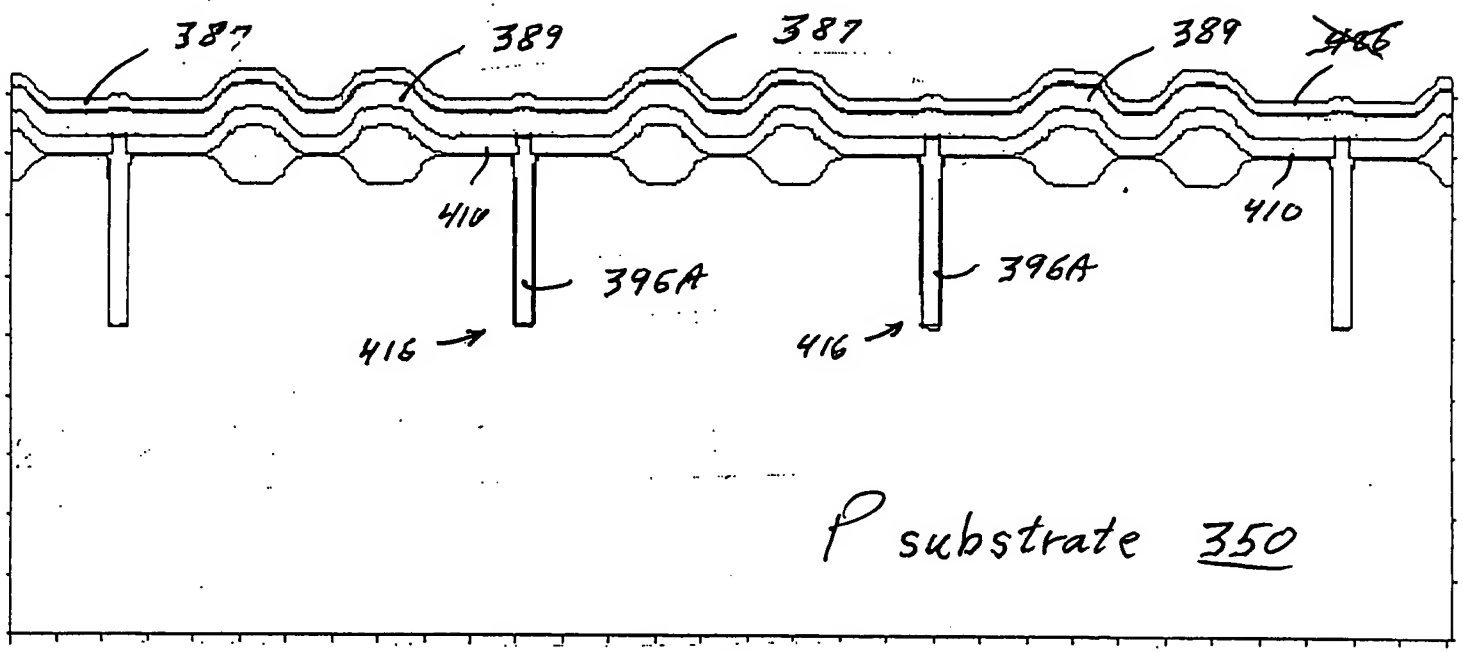


Fig. 19G

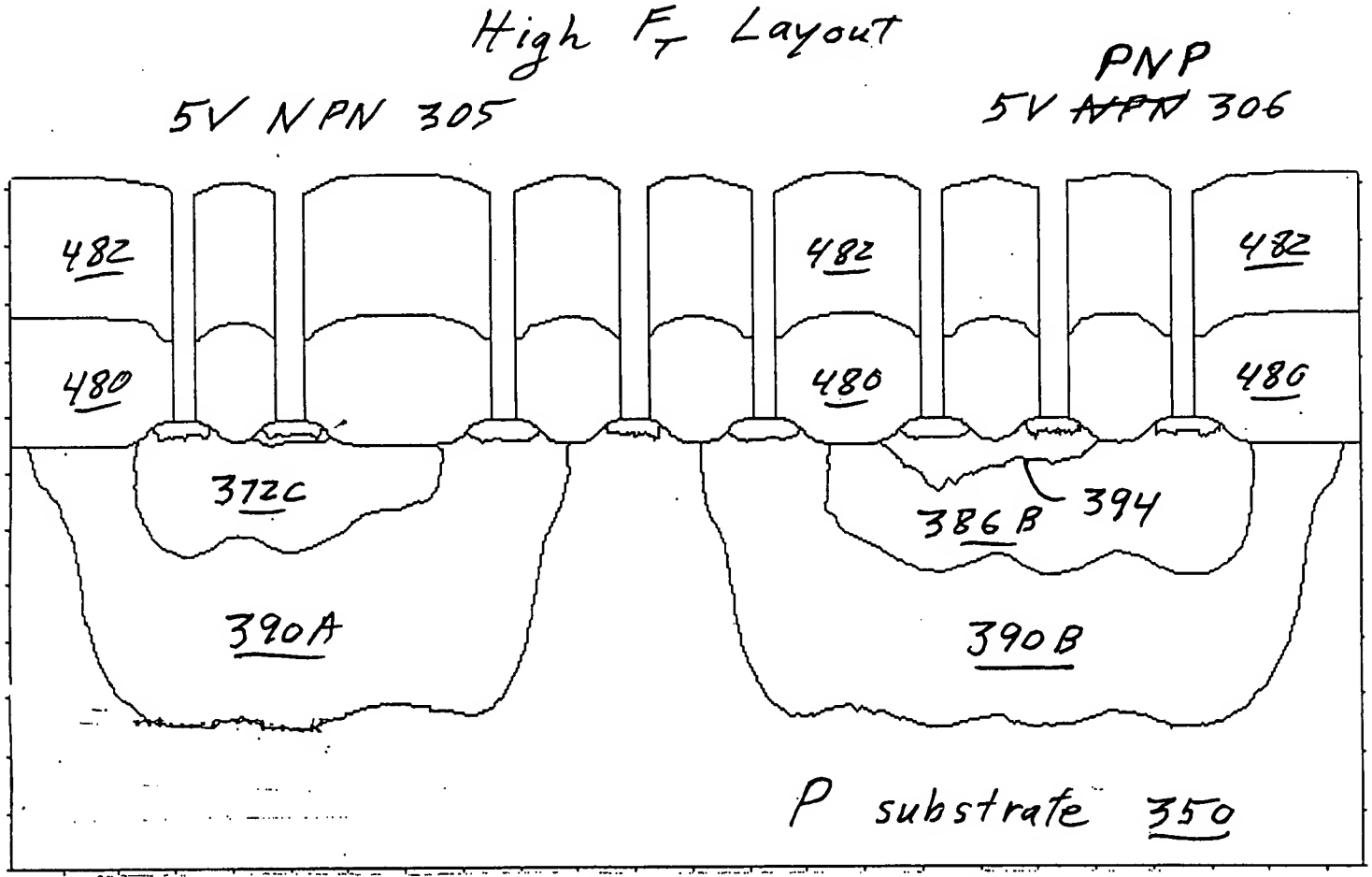
Fig. 19F

30V Lateral Trench DMOS 308



Interlayer Dielectric

Fig 33D



Interlayer Dielectric Deposition and Etch

Fig. 64B

Fig. 17U

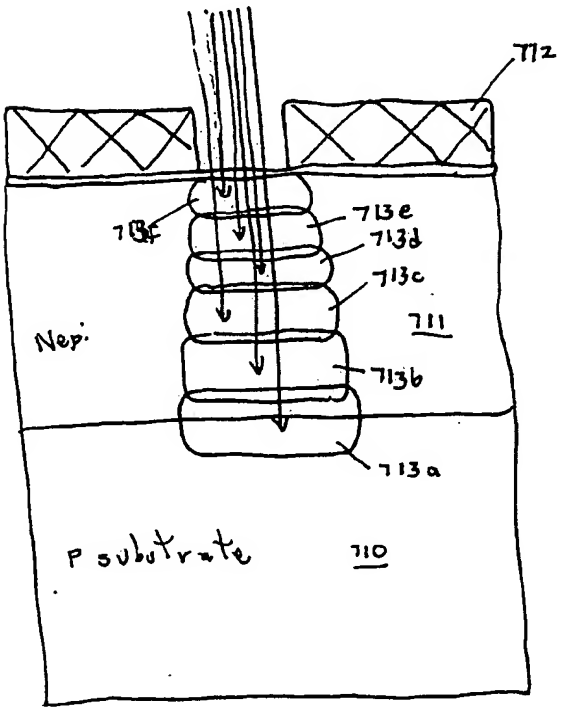


Fig. 17V

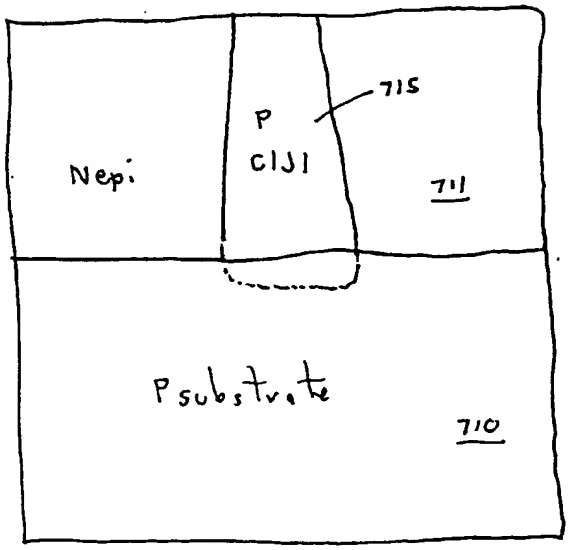


Fig. 17W

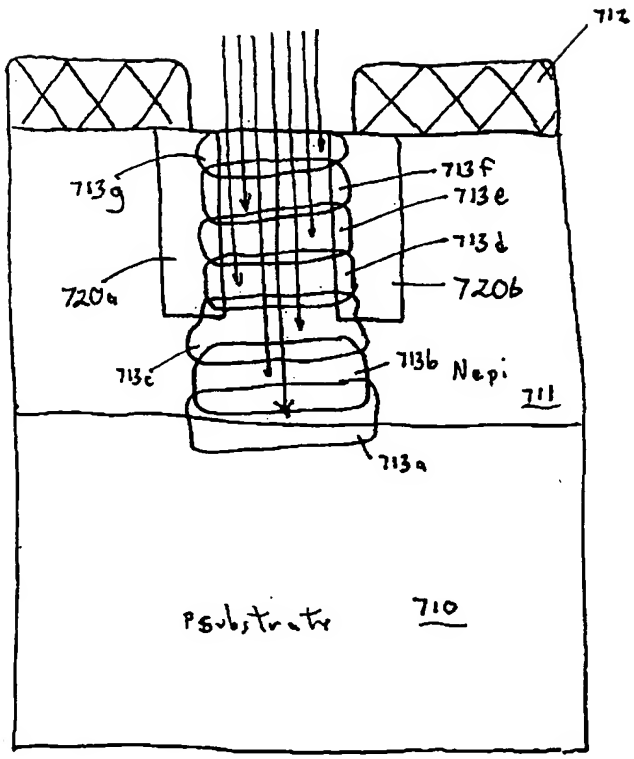
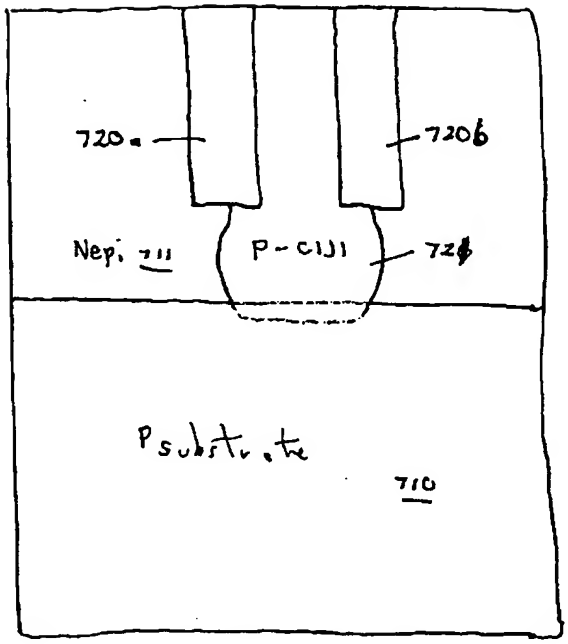
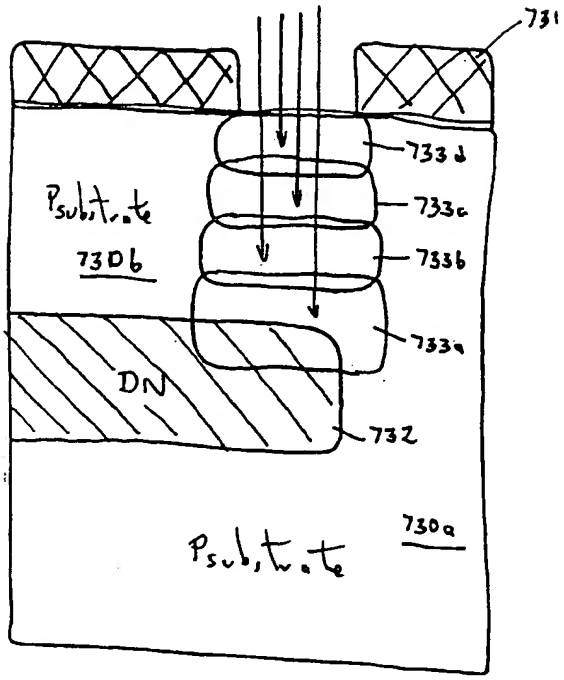


Fig. 17X



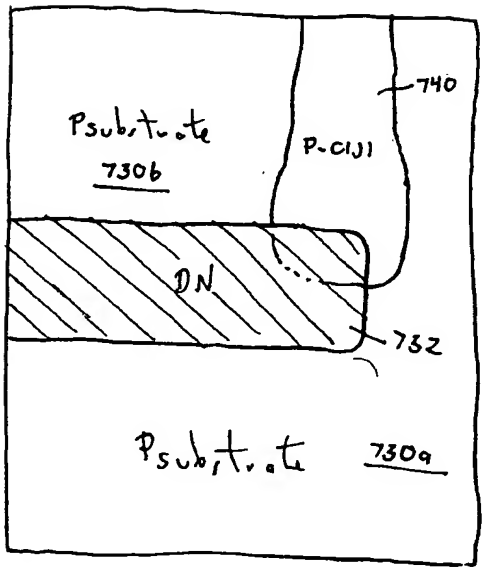
Y

Fig. 17Y



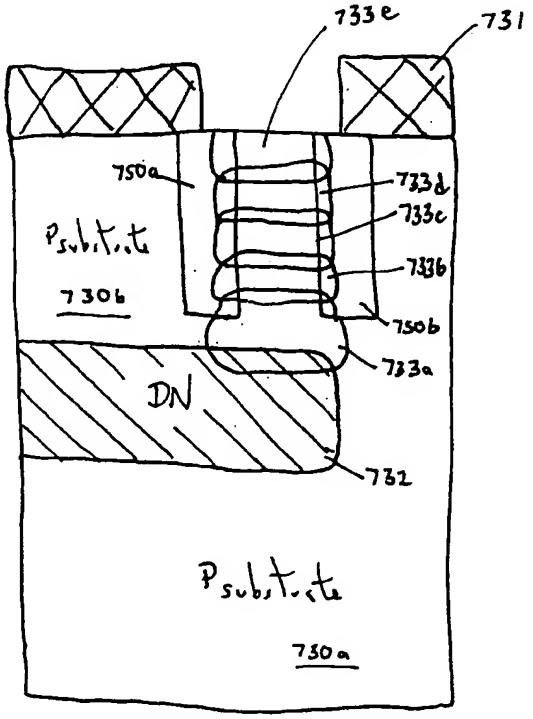
Z

Fig. 17Z



AA

Fig. 17~~BB~~



BB

Fig. 17~~c~~

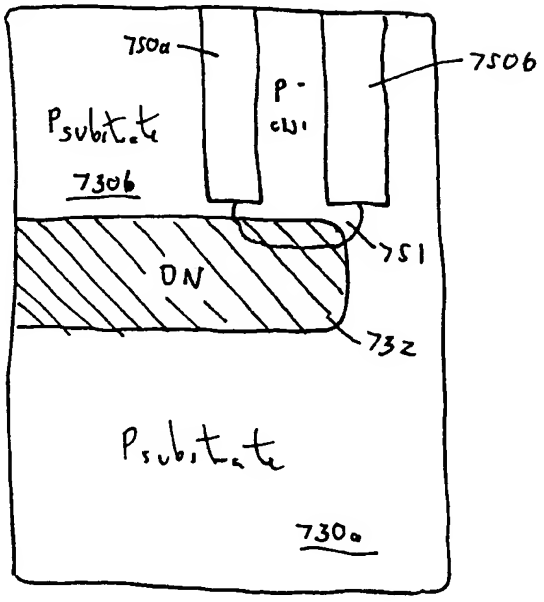
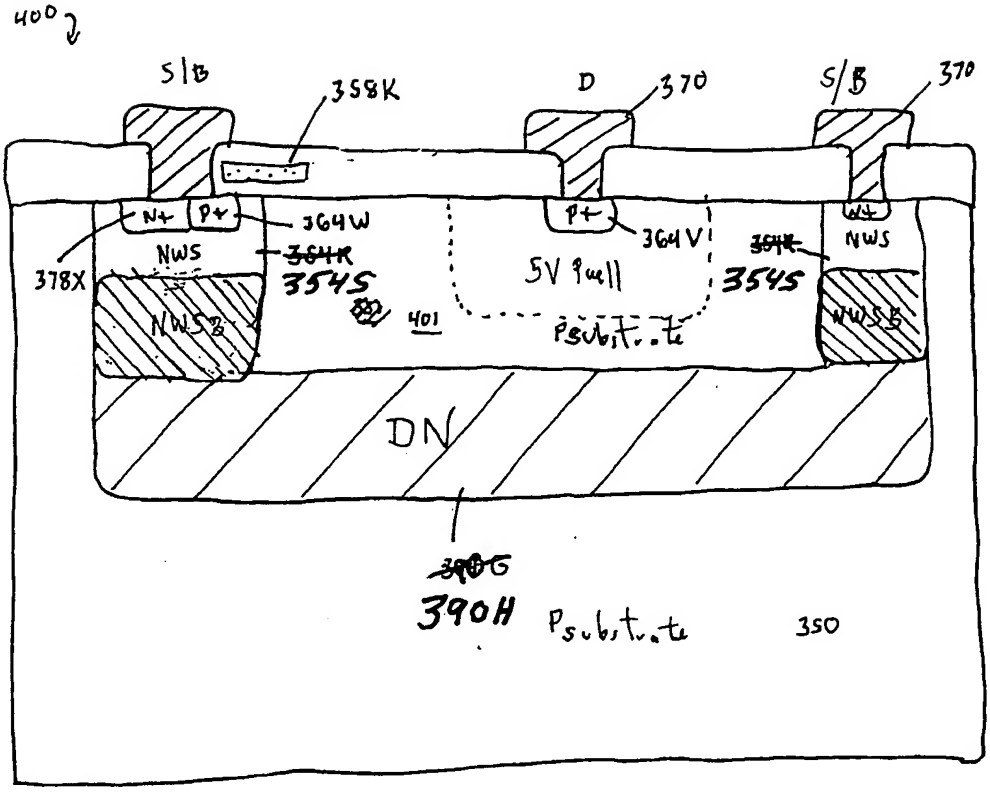


Fig. 18H


400
S/B
358K
D
370
S/B
370
N+
P+
364W
P+
364V
W+
NWS
354R
354S
5V well
354R
354S
NWS
378X
NWSB
401
Psubstrate
NWSB
DN
390G
390H
Psubstrate
350